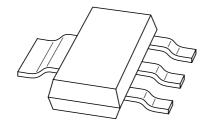
# **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# **BAT120 series**Schottky barrier double diodes

Product data sheet Supersedes data of 2001 Aug 27 2003 Aug 04



# Schottky barrier double diodes

# **BAT120** series

### **FEATURES**

- · Low switching losses
- · Capability of absorbing very high surge current
- Fast recovery time
- · Guard ring protected
- Plastic SMD package.

### **APPLICATIONS**

- Low power switched-mode power supplies
- Rectification
- · Polarity protection.

### **DESCRIPTION**

Planar Schottky barrier double diodes encapsulated in a SOT223 plastic SMD package.

### **MARKING**

TYPE NUMBER	MARKING CODE
BAT120A	AT120A
BAT120C	AT120C
BAT120S	AT120S

### **PINNING**

DIN	BAT120						
PIN	Α	С	S				
1	k <sub>1</sub>	a <sub>1</sub>	a <sub>1</sub>				
2	n.c.	n.c.	n.c.				
3	k <sub>2</sub>	$a_2$	k <sub>2</sub>				
4	a <sub>1</sub> , a <sub>2</sub>	k <sub>1</sub> , k <sub>2</sub>	k <sub>1</sub> , a <sub>2</sub>				

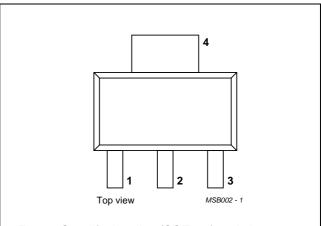
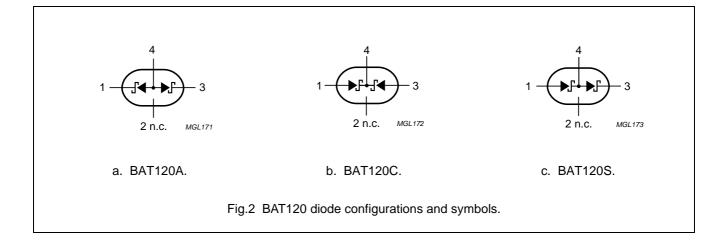


Fig.1 Simplified outline (SOT223) and pin configuration.



# Schottky barrier double diodes

BAT120 series

# **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V <sub>R</sub>	continuous reverse voltage		_	25	V
I <sub>F</sub>	continuous forward current		_	1	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ < 10 ms; half sinewave; JEDEC method	-	10	А
I <sub>RSM</sub>	non-repetitive peak reverse current	t <sub>p</sub> = 100 μs	_	0.5	Α
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	125	°C
T <sub>amb</sub>	operating ambient temperature		-65	+125	°C

# **ELECTRICAL CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
Per diode			•		
V <sub>F</sub>	forward voltage	see Fig.3			
		I <sub>F</sub> = 100 mA	260	300	mV
		I <sub>F</sub> = 1 A	400	450	mV
I <sub>R</sub>	reverse current	V <sub>R</sub> = 20 V; note 1; see Fig.4	80	500	μΑ
		V <sub>R</sub> = 25 V; note 1; see Fig.4	_	1	mA
		$V_R = 20 \text{ V}; T_j = 100 ^{\circ}\text{C}; \text{ note } 1$	_	10	mA
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 4 V; see Fig.5	100	_	pF

# Note

1. Pulse test:  $t_p$  = 300  $\mu$ s;  $\delta$  = 0.02.

# THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	100	K/W

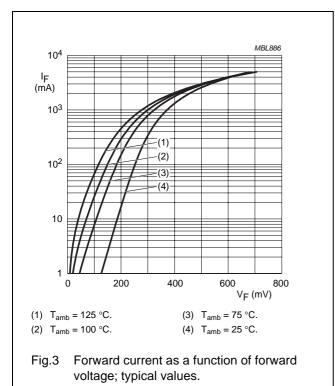
### Note

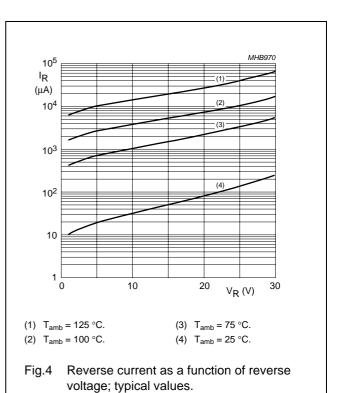
1. Refer to SOT223 standard mounting conditions.

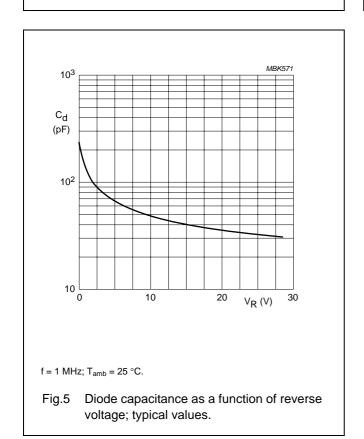
# Schottky barrier double diodes

# BAT120 series

# **GRAPHICAL DATA**







4

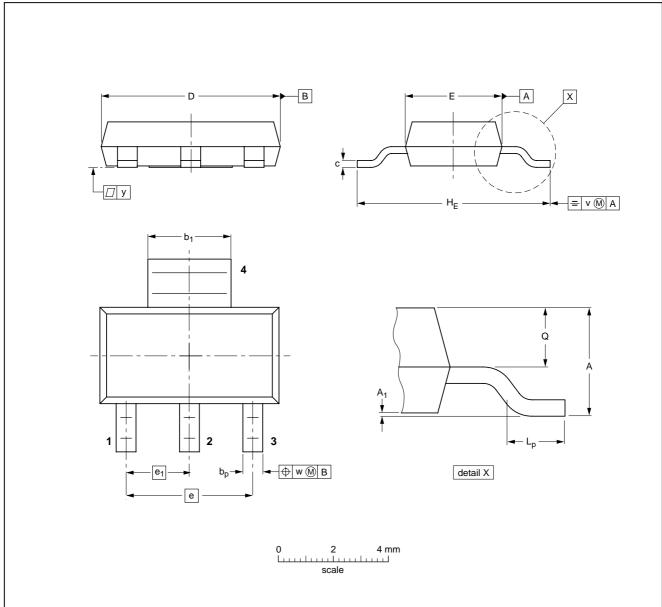
# Schottky barrier double diodes

# BAT120 series

# **PACKAGE OUTLINE**

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

**SOT223** 



# DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	bp	b <sub>1</sub>	С	D	E	е	e <sub>1</sub>	HE	Lp	Q	v	w	у
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT223			SC-73			<del>97-02-28</del> 99-09-13

# Schottky barrier double diodes

BAT120 series

### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

### **Notes**

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- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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# **Contact information**

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